



100V N-Channel Enhancement Mode MOSFET

Voltage

100 V

Current

18A

Features

- RDS(ON), VGS@10V, ID@18A<50mΩ
- RDS(ON), VGS@4.5V, ID@15A<55mΩ
- Advanced Trench Process Technology
- High density cell design for ultra low on-resistance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

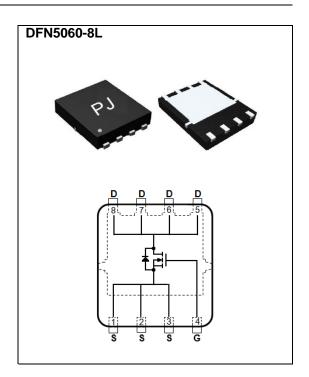
Mechanical Data

• Case: DFN5060-8L Package

• Terminals: Solderable per MIL-STD-750, Method 2026

Approx. Weight: 0.0028 ounces, 0.08 grams

Marking: Q5474A



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V _{DS}	100	V
Gate-Source Voltage		V_{GS}	<u>+</u> 20	V
Continuous Drain Current		I _D	18	Α
Pulsed Drain Current		I _{DM}	36	Α
Single Pulse Avalanche Energy (Note 5)		E _{AS}	16.2	mJ
Power Dissipation	T _C =25°C	P_{D}	52	W
	Derate above 25°C		416	mW/°C
Operating Junction and Storage Temperature Range		T_J, T_{STG}	-55~150	°C
Typical Thermal resistance - Junction to Ambient, t<10s (Note 3)		R _{eJC}	2.4	°C/W





Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS		
Static								
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V,I _D =250uA	100	-	-	V		
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_{D}=250uA$	1.0	1.5	2.5	V		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =18A	-	37	50	mΩ		
		V _{GS} =4.5V,I _D =15A	-	38	55			
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =80V,V _{GS} =0V	-	0.03	1.0	uA		
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 20V,V _{DS} =0V	-	<u>+</u> 10	<u>+</u> 100	nA		
Dynamic (Note 7)								
Total Gate Charge	Q_g	V _{DS} =80V, I _D =18A, V _{GS} =10V (Note 1,2)	-	61	-	nC		
Gate-Source Charge	Q_gs		-	8.8	-			
Gate-Drain Charge	Q_gd		-	11	-			
Input Capacitance	Ciss	V _{DS} =15V, V _{GS} =0V, f=1.0MHZ	-	3555	-	pF		
Output Capacitance	Coss		-	119	-			
Reverse Transfer Capacitance	Crss		-	56	-			
Turn-On Delay Time	td _(on)	V_{DD} =50V, I_{D} =18A, V_{GS} =10V, R_{G} =3.3 Ω (Note 1,2)	-	16	-	ns		
Turn-On Rise Time	tr		-	50	-			
Turn-Off Delay Time	td _(off)		-	64	-			
Turn-Off Fall Time	tf		-	18	-			
Drain-Source Diode								
Maximum Continuous Drain-Source				-	18	А		
Diode Forward Current	I _S		_					
Diode Forward Voltage	V _{SD}	I _S =1.0A, V _{GS} =0V	-	0.7	1.2	V		

NOTES:

- 1. Pulse width<300us, Duty cycle<2%
- 2. Essentially independent of operating temperature typical characteristics.
- 3. The maximum current rating is package limited.
- 4. Repetitive rating, pulse width limited by junction temperature TJ(MAX)=150°C. Ratings are based on low frequency and duty cycles to keep initial TJ =25°C.
- 5. The test condition is L=0.1mH, I_{AS} =18A, V_{DD} =25V, V_{GS} =10V
- 6. Rejah is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 7. Guaranteed by design, not subject to production testing.





TYPICAL CHARACTERISTIC CURVES

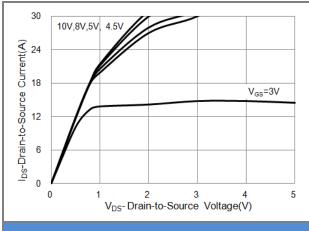


Fig.1 On-Region Characteristics

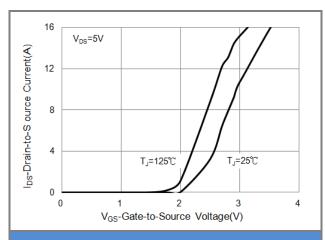


Fig.2 Transfer Characteristics

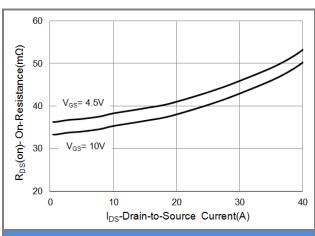


Fig.3 On-Resistance vs. Drain Current

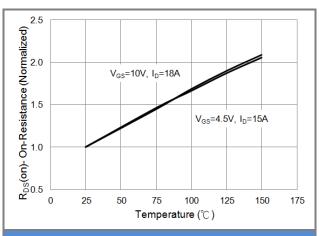


Fig.4 On-Resistance vs. Junction temperature

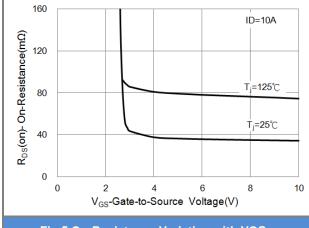
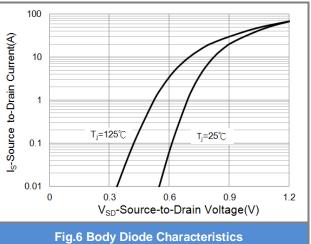


Fig.5 On-Resistance Variation with VGS.







TYPICAL CHARACTERISTIC CURVES

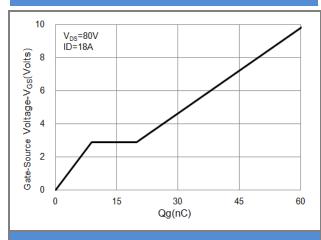


Fig.7 Gate-Charge Characteristics

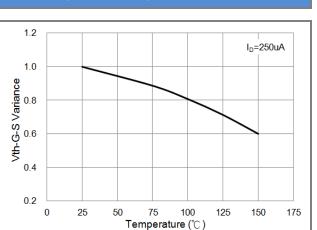
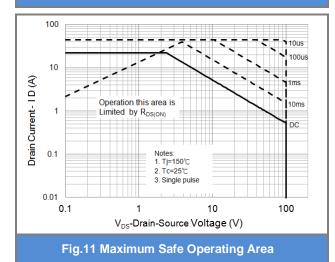


Fig.9 Threshold Voltage Variation with Temperature.



1.1 | I_D=250uA |

Fig.8 Breakdown Voltage Variation vs. Temperature

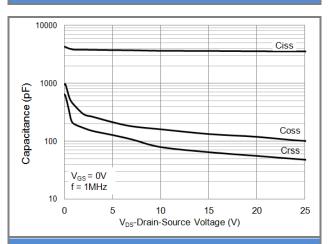


Fig.10 Capacitance vs. Drain-Source Voltage.





TYPICAL CHARACTERISTIC CURVES

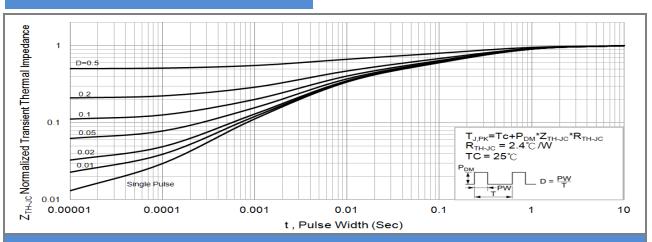


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

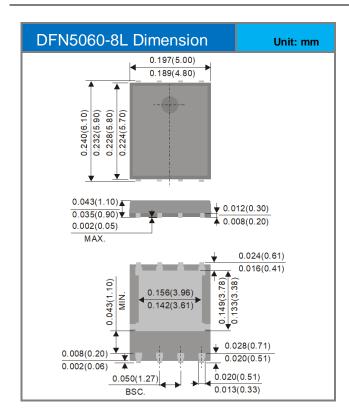


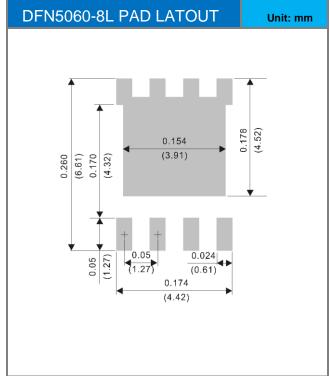


PART NO PACKING CODE VERSION

Part No Packing Code	Package Type	Packing type	Marking	Version
PJQ5474A_R2_00001	DFN5060-8L	3000pcs / 13" reel	Q5474A	Halogen free

Packaging Information & Mounting Pad Layout









Disclaimer

- Reproducing and modifying information of the document is prohibited without permission from Panjit International Inc..
- Panjit International Inc. reserves the rights to make changes of the content herein the document anytime without notification. Please refer to our website for the latest document.
- Panjit International Inc. disclaims any and all liability arising out of the application or use of any product including damages incidentally and consequentially occurred.
- Panjit International Inc. does not assume any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.
- Applications shown on the herein document are examples of standard use and operation. Customers are
 responsible in comprehending the suitable use in particular applications. Panjit International Inc. makes no
 representation or warranty that such applications will be suitable for the specified use without further testing or
 modification.
- The products shown herein are not designed and authorized for equipments requiring high level of reliability or relating to human life and for any applications concerning life-saving or life-sustaining, such as medical instruments, transportation equipment, aerospace machinery et cetera. Customers using or selling these products for use in such applications do so at their own risk and agree to fully indemnify Panjit International Inc. for any damages resulting from such improper use or sale.
- Since Panjit uses lot number as the tracking base, please provide the lot number for tracking when complaining.